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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

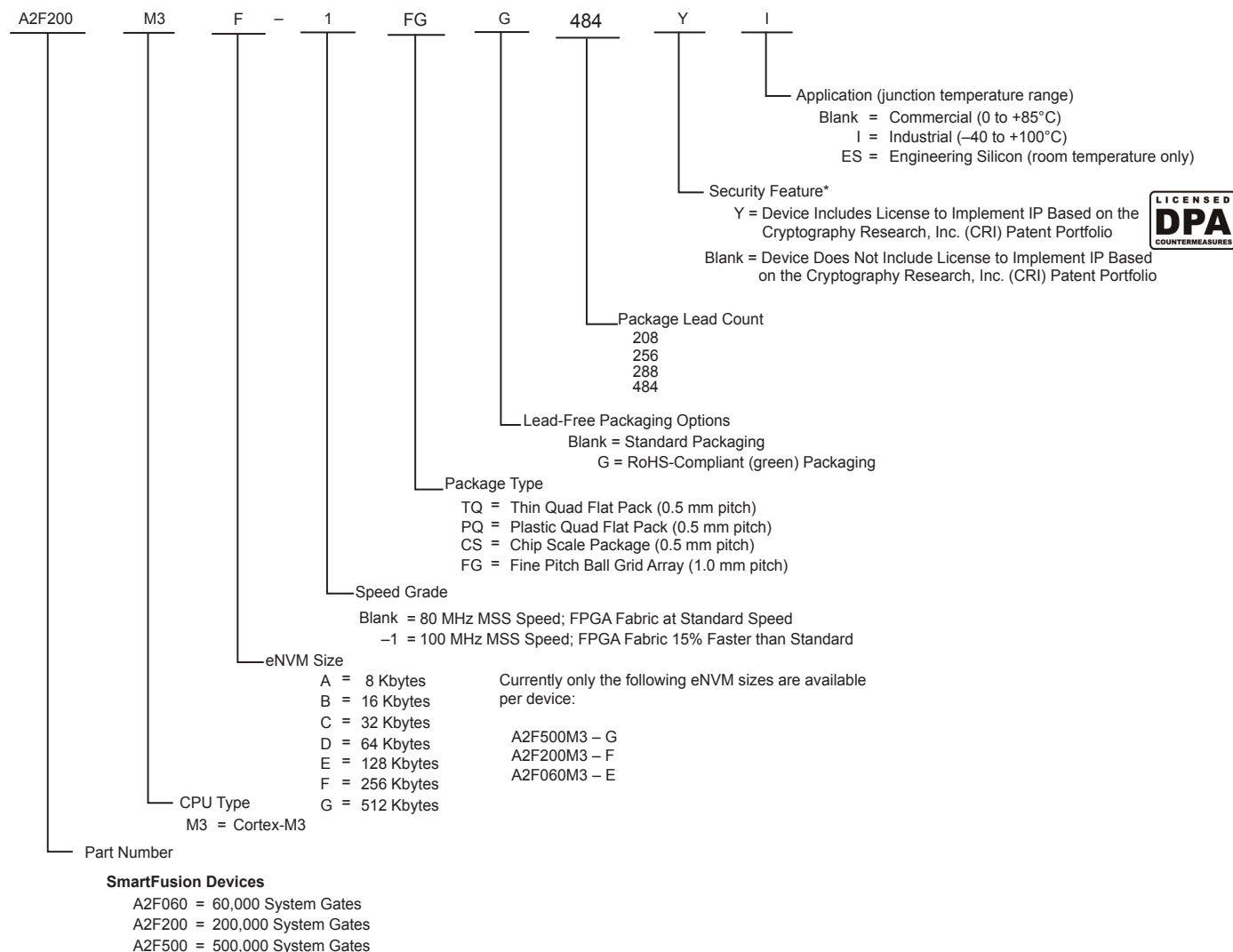
What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Obsolete
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	Ethernet, I ² C, SPI, UART/USART
Speed	80MHz
Primary Attributes	ProASIC®3 FPGA, 500K Gates, 11520 D-Flip-Flops
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f500m3g-pq208

Product Ordering Codes



Note: *Most devices in the SmartFusion cSoC family can be ordered with the Y suffix. Devices with a package size greater or equal to 5x5 mm are supported. Contact your local Microsemi SoC Products Group sales representative for more information.

Temperature Grade Offerings

SmartFusion cSoC	A2F060	A2F200	A2F500
TQ144	C, I	—	—
PQ208	—	C, I	C, I
CS288	C, I	C, I	C, I
FG256	C, I	C, I	C, I
FG484	—	C, I	C, I

Notes:

1. C = Commercial Temperature Range: 0°C to 85°C Junction
2. I = Industrial Temperature Range: -40°C to 100°C Junction

SmartFusion Family Overview

Introduction	1-1
General Description	1-1

SmartFusion DC and Switching Characteristics

General Specifications	2-1
Calculating Power Dissipation	2-10
User I/O Characteristics	2-19
VersaTile Characteristics	2-55
Global Resource Characteristics	2-59
RC Oscillator	2-61
Main and Lower Power Crystal Oscillator	2-62
Clock Conditioning Circuits	2-63
FPGA Fabric SRAM and FIFO Characteristics	2-65
Embedded Nonvolatile Memory Block (eNVM)	2-76
Embedded FlashROM (eFROM)	2-76
JTAG 1532 Characteristics	2-76
Programmable Analog Specifications	2-78
Serial Peripheral Interface (SPI) Characteristics	2-89
Inter-Integrated Circuit (I ² C) Characteristics	2-91

SmartFusion Development Tools

Types of Design Tools	3-1
SmartFusion Ecosystem	3-3
Middleware	3-5
References	3-6

SmartFusion Programming

In-System Programming	4-7
In-Application Programming	4-8
Typical Programming and Erase Times	4-9
References	4-9

Pin Descriptions

Supply Pins	5-1
User-Defined Supply Pins	5-5
Global I/O Naming Conventions	5-6
User Pins	5-6
Special Function Pins	5-8
JTAG Pins	5-10
Microcontroller Subsystem (MSS)	5-12
Analog Front-End (AFE)	5-14
Analog Front-End Pin-Level Function Multiplexing	5-16
TQ144	5-18
CS288	5-23
PQ208	5-34
FG256	5-42
FG484	5-52

Datasheet Information

List of Changes	6-1
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1 – SmartFusion Family Overview

Introduction

The SmartFusion® family of cSoCs builds on the technology first introduced with the Fusion mixed signal FPGAs. SmartFusion cSoCs are made possible by integrating FPGA technology with programmable high-performance analog and hardened ARM Cortex-M3 microcontroller blocks on a flash semiconductor process. The SmartFusion cSoC takes its name from the fact that these three discrete technologies are integrated on a single chip, enabling the lowest cost of ownership and smallest footprint solution to you.

General Description

Microcontroller Subsystem (MSS)

The MSS is composed of a 100 MHz Cortex-M3 processor and integrated peripherals, which are interconnected via a multi-layer AHB bus matrix (ABM). This matrix allows the Cortex-M3 processor, FPGA fabric master, Ethernet media access controller (MAC), when available, and peripheral DMA (PDMA) controller to act as masters to the integrated peripherals, FPGA fabric, embedded nonvolatile memory (eNVM), embedded synchronous RAM (eSRAM), external memory controller (EMC), and analog compute engine (ACE) blocks.

SmartFusion cSoCs of different densities offer various sets of integrated peripherals. Available peripherals include SPI, I²C, and UART serial ports, embedded FlashROM (EFROM), 10/100 Ethernet MAC, timers, phase-locked loops (PLLs), oscillators, real-time counters (RTC), and peripheral DMA controller (PDMA).

Programmable Analog

Analog Front-End (AFE)

SmartFusion cSoCs offer an enhanced analog front-end compared to Fusion devices. The successive approximation register analog-to-digital converters (SAR ADC) are similar to those found on Fusion devices. SmartFusion cSoC also adds first order sigma-delta digital-to-analog converters (SDD DAC).

SmartFusion cSoCs can handle multiple analog signals simultaneously with its signal conditioning blocks (SCBs). SCBs are made of a combination of active bipolar prescalers (ABPS), comparators, current monitors and temperature monitors. ABPS modules allow larger bipolar voltages to be fed to the ADC. Current monitors take the voltage across an external sense resistor and convert it to a voltage suitable for the ADC input range. Similarly, the temperature monitor reads the current through an external PN-junction (diode or transistor) and converts it internally for the ADC. The SCB also includes comparators to monitor fast signal thresholds without using the ADC. The output of the comparators can be fed to the analog compute engine or the ADC.

Analog Compute Engine (ACE)

The mixed signal blocks found in SmartFusion cSoCs are controlled and connected to the rest of the system via a dedicated processor called the analog compute engine (ACE). The role of the ACE is to offload control of the analog blocks from the Cortex-M3, thus offering faster throughput or better power consumption compared to a system where the main processor is in charge of monitoring the analog resources. The ACE is built to handle sampling, sequencing, and post-processing of the ADCs, DACs, and SCBs.

Standby Mode

$$P_{\text{DYN}} = P_{\text{RC-OSC}} + P_{\text{LPXTAL-OSC}}$$

Time Keeping Mode

$$P_{\text{DYN}} = P_{\text{LPXTAL-OSC}}$$

Global Clock Dynamic Contribution— P_{CLOCK} **SoC Mode**

$$P_{\text{CLOCK}} = (P_{\text{AC1}} + N_{\text{SPINE}} * P_{\text{AC2}} + N_{\text{ROW}} * P_{\text{AC3}} + N_{\text{S-CELL}} * P_{\text{AC4}}) * F_{\text{CLK}}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Device Architecture" chapter of the [SmartFusion FPGA Fabric User's Guide](#).

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Device Architecture" chapter of the [SmartFusion FPGA Fabric User's Guide](#).

F_{CLK} is the global clock signal frequency.

$N_{\text{S-CELL}}$ is the number of VersaTiles used as sequential modules in the design.

Standby Mode and Time Keeping Mode

$$P_{\text{CLOCK}} = 0 \text{ W}$$

Sequential Cells Dynamic Contribution— $P_{\text{S-CELL}}$ **SoC Mode**

$$P_{\text{S-CELL}} = N_{\text{S-CELL}} * (P_{\text{AC5}} + (\alpha_1 / 2) * P_{\text{AC6}}) * F_{\text{CLK}}$$

$N_{\text{S-CELL}}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$$P_{\text{S-CELL}} = 0 \text{ W}$$

Combinatorial Cells Dynamic Contribution— $P_{\text{C-CELL}}$ **SoC Mode**

$$P_{\text{C-CELL}} = N_{\text{C-CELL}} * (\alpha_1 / 2) * P_{\text{AC7}} * F_{\text{CLK}}$$

$N_{\text{C-CELL}}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$$P_{\text{C-CELL}} = 0 \text{ W}$$

Routing Net Dynamic Contribution— P_{NET} **SoC Mode**

$$P_{\text{NET}} = (N_{\text{S-CELL}} + N_{\text{C-CELL}}) * (\alpha_1 / 2) * P_{\text{AC8}} * F_{\text{CLK}}$$

$N_{\text{S-CELL}}$ is the number VersaTiles used as sequential modules in the design.

$N_{\text{C-CELL}}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the frequency of the clock driving the logic including these nets.

Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings
–1 Speed Grade, Worst Commercial-Case Conditions: T_J = 85°C, Worst Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx (per standard)
Applicable to FPGA I/O Banks, Assigned to EMC I/O Pins

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t _{BOU} T (ns)	t _{DP} (ns)	t _{DIN} (ns)	t _{PY} (ns)	t _{EOU} T (ns)	t _{ZL} (ns)	t _{ZH} (ns)	t _{LZ} (ns)	t _{HZ} (ns)	t _{ZLS} (ns)	t _{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
2.5 V LVCMOS	12 mA	High	35	–	0.50	2.73	0.03	1.03	0.32	2.88	2.69	2.62	2.70	4.60	4.41	ns
1.8 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
1.5 V LVCMOS	12 mA	High	35	–	0.50	3.24	0.03	1.12	0.32	3.30	2.79	3.10	3.27	5.02	4.50	ns
3.3 V PCI	Per PCI spec	High	10	25 ¹	0.50	2.11	0.03	0.68	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
3.3 V PCI-X	Per PCI-X spec	High	10	25 ¹	0.50	2.11	0.03	0.64	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
LVDS	24 mA	High	–	–	0.50	1.53	0.03	1.55	–	–	–	–	–	–	–	ns
LVPECL	24 mA	High	–	–	0.50	1.46	0.03	1.46	–	–	–	–	–	–	–	ns

Notes:

1. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-10 on page 2-39](#) for connectivity. This resistor is not required during normal operation.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings
–1 Speed Grade, Worst Commercial-Case Conditions: T_J = 85°C, Worst Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx (per standard)
Applicable to MSS I/O Banks

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor	t _{DOUT} (ns)	t _{DP} (ns)	t _{DIN} (ns)	t _{PY} (ns)	t _{PYS} (ns)	t _{EOUT} (ns)	t _{ZL} (ns)	t _{ZH} (ns)	t _{LZ} (ns)	t _{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	High	10	–	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns
2.5 V LVCMOS	8 mA	High	10	–	0.18	1.96	0.07	0.99	1.16	0.18	2.00	1.82	1.82	1.93	ns
1.8 V LVCMOS	4 mA	High	10	–	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns
1.5 V LVCMOS	2 mA	High	10	–	0.18	2.70	0.07	1.07	1.55	0.18	2.75	2.67	1.87	1.85	ns

Notes:

1. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-10 on page 2-39](#) for connectivity. This resistor is not required during normal operation.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

Table 2-35 • Minimum and Maximum DC Input and Output Levels
Applicable to FPGA I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	15	15
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	15	15
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	15	15
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	15	15
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	15	15
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	15	15
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. Currents are measured at 100°C junction temperature and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Software default selection highlighted in gray.

Table 2-36 • Minimum and Maximum DC Input and Output Levels
Applicable to MSS I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	15	15

Notes:

1. Currents are measured at 100°C junction temperature and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Software default selection highlighted in gray.

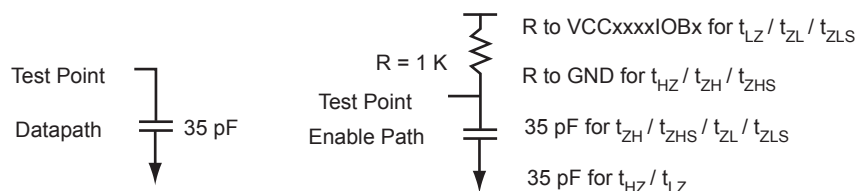


Figure 2-6 • AC Loading

Table 2-37 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	CLOAD (pF)
0	3.3	1.4	—	35

Note: *Measuring point = V_{trip} . See Table 2-22 on page 2-24 for a complete table of trip points.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-53 • Minimum and Maximum DC Input and Output Levels
Applicable to FPGA I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	−0.3	0.35 *	0.65 *	1.575	0.25*	0.75 *	2	2	16	13	15	15
		VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						
4 mA	−	0.35*	0.65 *	1.575	0.25*	0.75 *	4	4	33	25	15	15
	0.3	VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						
6 mA	−	0.35 *	0.65 *	1.575	0.25*	0.75 *	6	6	39	32	15	15
	0.3	VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						
8 mA	−	0.35 *	0.65 *	1.575	0.25* VCC	0.75 *	8	8	55	66	15	15
	0.3	VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						
12 mA	−	0.35 *	0.65 *	1.575	0.25 *	0.75 *	12	12	55	66	15	15
	0.3	VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Software default selection highlighted in gray.

Table 2-54 • Minimum and Maximum DC Input and Output Levels
Applicable to MSS I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	−0.3	0.35 *	0.65 *	1.575	0.25 *	0.75 *	2	2	16	13	15	15
		VCCxxxxIOBx	VCCxxxxIOBx		VCCxxxxIOBx	VCCxxxxIOBx						

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Software default selection highlighted in gray.

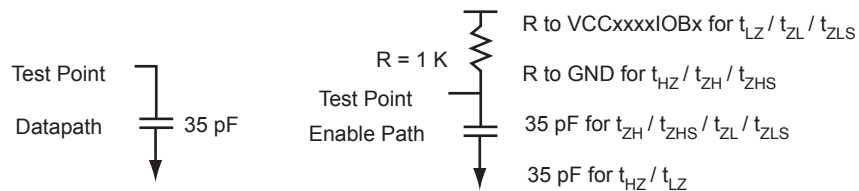


Figure 2-9 • AC Loading

Table 2-55 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	CLOAD (pF)
0	1.5	0.75	−	35

* Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.

Table 2-66 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCFPGAIOBx	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V _{REF} (typ.) (V)
1.64	1.94	Cross point	–

* Measuring point = V_{trip} . See [Table 2-22 on page 2-24](#) for a complete table of trip points.

Timing Characteristics

Table 2-68 • LVPECL

Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst-Case VCC = 1.425 V,

Worst-Case VCCFPGAIOBx = 3.0 V

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.60	1.76	0.04	1.76	ns
–1	0.50	1.46	0.03	1.46	ns

Notes:

- For the derating values at specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.
- The above mentioned timing parameters correspond to 24mA drive strength.

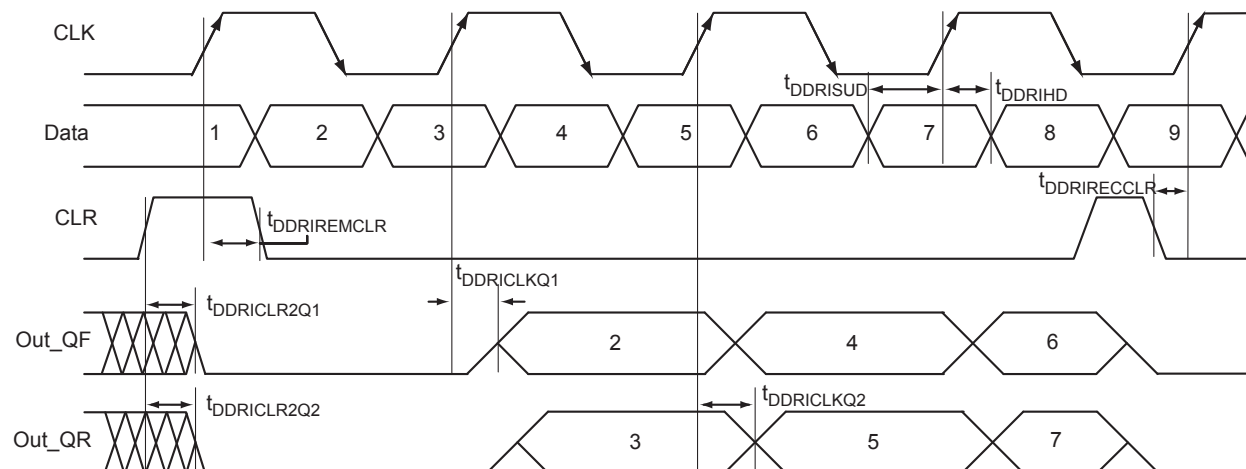


Figure 2-20 • Input DDR Timing Diagram

Timing Characteristics

Table 2-75 • Input DDR Propagation Delays

Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Units
t_{DDRICKQ1}	Clock-to-Out Out_QR for Input DDR	0.39	ns
t_{DDRICKQ2}	Clock-to-Out Out_QF for Input DDR	0.28	ns
t_{DDRISUD}	Data Setup for Input DDR	0.29	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	ns
$t_{\text{DDRICLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.58	ns
$t_{\text{DDRICLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.47	ns
t_{DDRIMCLR}	Asynchronous Clear Removal time for Input DDR	0.00	ns
t_{DDRIMCLR}	Asynchronous Clear Recovery time for Input DDR	0.23	ns
t_{DDRIMCLR}	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	ns
t_{DDRIMCLR}	Clock Minimum Pulse Width High for Input DDR	0.36	ns
t_{DDRIMCLR}	Clock Minimum Pulse Width Low for Input DDR	0.32	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	350	MHz

Note: For derating values at specific junction temperature and voltage-supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

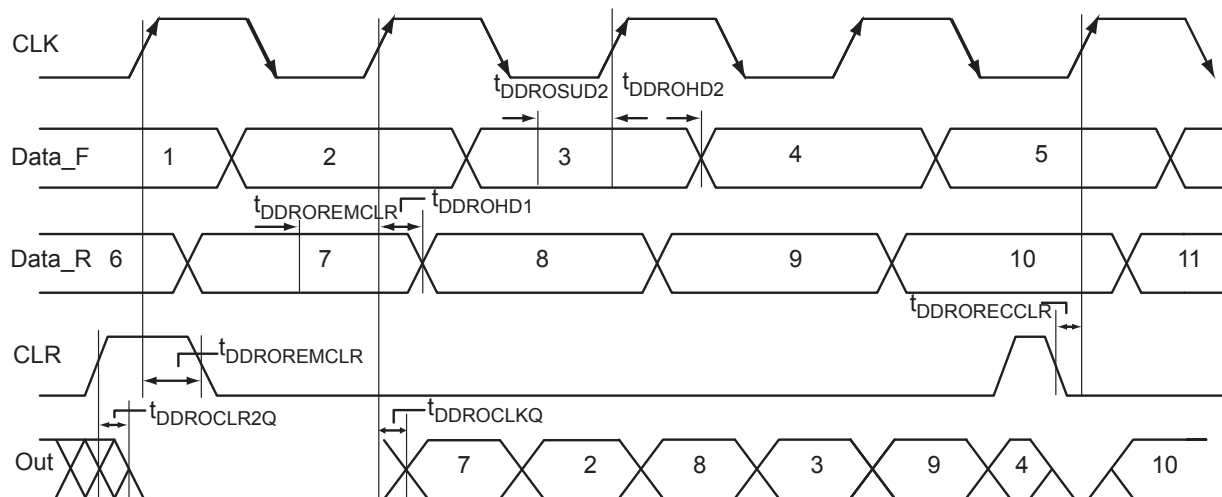


Figure 2-22 • Output DDR Timing Diagram

Timing Characteristics

Table 2-77 • Output DDR Propagation Delays

Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	0.71	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.38	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.38	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	0.81	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.36	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	350	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The SmartFusion library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [IGLOO/e](#), [Fusion](#), [ProASIC3/E](#), and [SmartFusion Macro Library Guide](#).

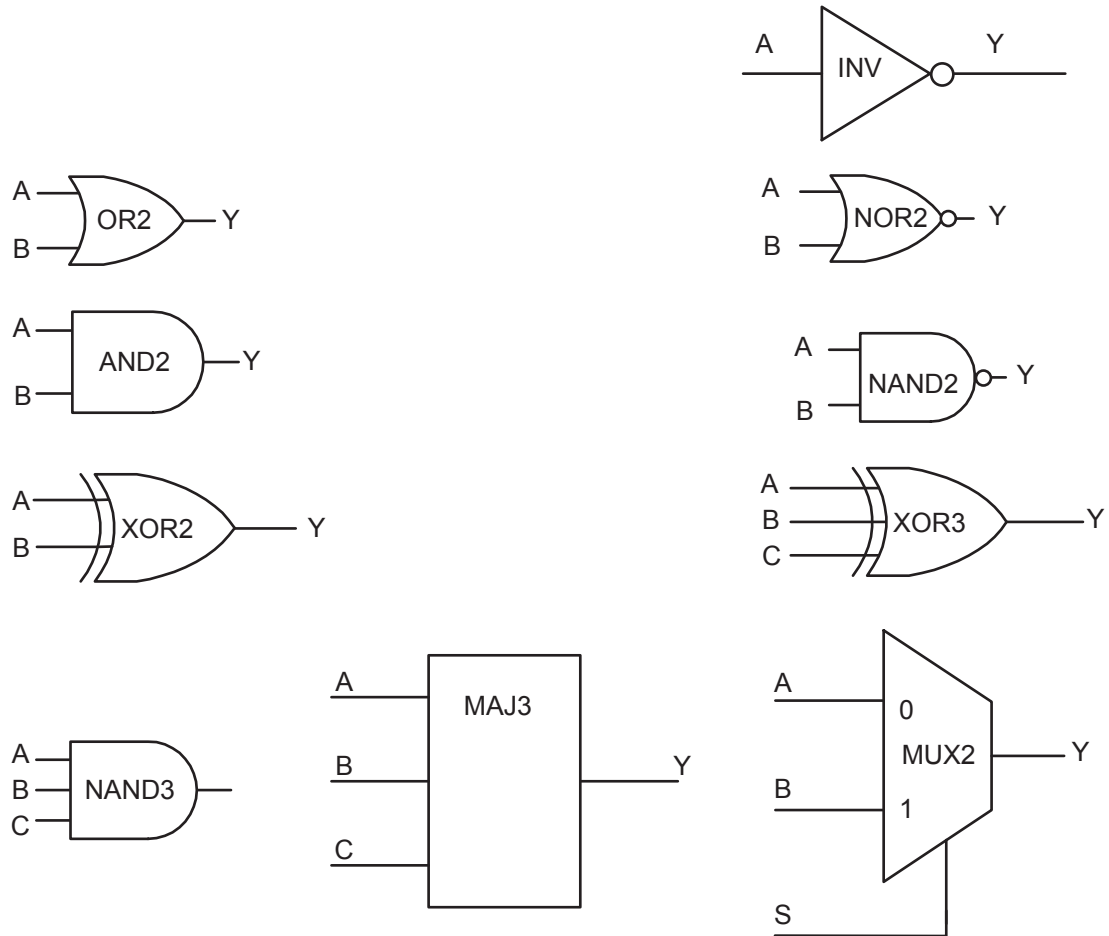


Figure 2-23 • Sample of Combinatorial Cells

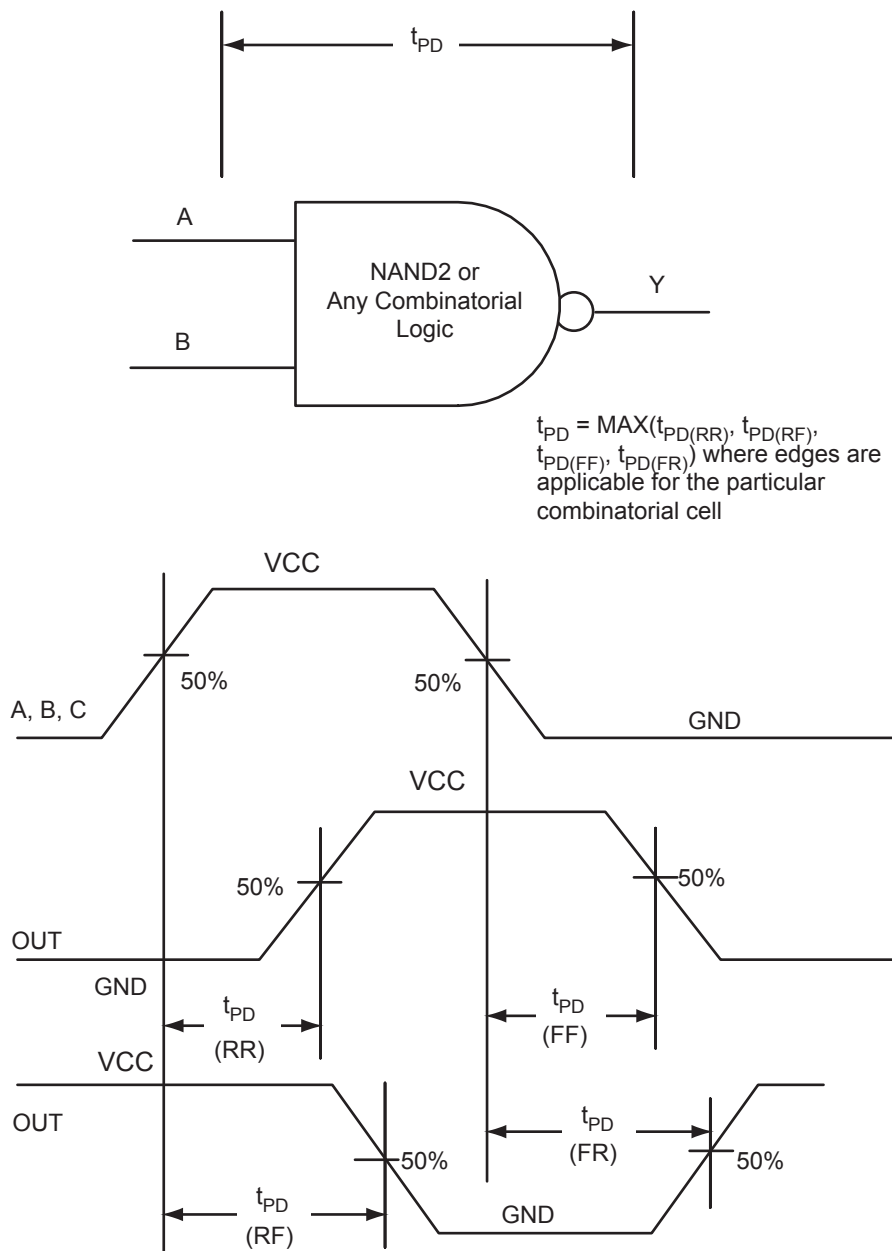


Figure 2-24 • Timing Model and Waveforms

Timing Characteristics

Table 2-87 • RAM4K9
Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.30	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.12	ns
t_{BKS}	BLK setup time	0.24	0.28	ns
t_{BKH}	BLK hold time	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.19	0.22	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.81	2.18	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.39	2.87	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.91	1.09	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—applicable to rising edge	0.23	0.26	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—applicable to opening edge	0.34	0.38	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address— applicable to opening edge	0.37	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.94	1.12	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.94	1.12	ns
$t_{REMRSTB}$	RESET removal	0.29	0.35	ns
$t_{RECRSTB}$	RESET recovery	1.52	1.83	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.22	0.22	ns
t_{CYC}	Clock cycle time	3.28	3.28	ns
F_{MAX}	Maximum clock frequency	305	305	MHz

Notes:

1. For more information, refer to the [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#) application note.
2. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Temperature Monitor

Unless otherwise noted, temperature monitor performance is specified with a 2N3904 diode-connected bipolar transistor from National Semiconductor or Infineon Technologies, nominal power supply voltages, with the output measured using the internal voltage reference with the internal ADC in 12-bit mode and 62.5 Ksps. After digital compensation. Unless otherwise noted, the specifications pertain to conditions where the SmartFusion cSoC and the sensing diode are at the same temperature.

Table 2-94 • Temperature Monitor Performance Specifications

Specification	Test Conditions	Min.	Typical	Max.	Units
Input diode temperature range		–55		150	°C
		233.2		378.15	K
Temperature sensitivity			2.5		mV/K
Intercept	Extrapolated to 0K		0		V
Input referred temperature offset error	At 25°C (298.15K)		±1	1.5	°C
Gain error	Slope of BFSL vs. 2.5 mV/K		±1	2.5	% nom.
Overall accuracy	Peak error from ideal transfer function		±2	±3	°C
Input referred noise	At 25°C (298.15K) – no output averaging		4		°C rms
Output current	Idle mode		100		µA
	Final measurement phases		10		µA
Analog settling time	Measured to 0.1% of final value, (with ADC load)				
	From TM_STB (High)	5			µs
	From ADC_START (High)	5		105	µs
AT parasitic capacitance				500	pF
Power supply rejection ratio	DC (0–10 KHz)	1.2	0.7		°C/V
Input referred temperature sensitivity error	Variation due to device temperature (–40°C to +100°C). External temperature sensor held constant.		0.005	0.008	°C/°C
Temperature monitor (TM) operational power supply current requirements (per temperature monitor instance, not including ADC or VAREF _x)	VCC33A		200		µA
	VCC33AP		150		µA
	VCC15A		50		µA

Note: All results are based on averaging over 64 samples.

Voltage Regulator

Table 2-99 • Voltage Regulator

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
V_{OUT}	Output voltage	$T_J = 25^{\circ}\text{C}$		1.425	1.5	1.575	V
V_{OS}	Output offset voltage	$T_J = 25^{\circ}\text{C}$			11		mV
ICC33A	Operation current	$T_J = 25^{\circ}\text{C}$	$I_{LOAD} = 1\text{ mA}$		3.4		mA
			$I_{LOAD} = 100\text{ mA}$		11		mA
			$I_{LOAD} = 0.5\text{ A}$		21		mA
ΔV_{OUT}	Load regulation	$T_J = 25^{\circ}\text{C}$	$I_{LOAD} = 1\text{ mA to }0.5\text{ A}$		5.8		mV
ΔV_{OUT}	Line regulation	$T_J = 25^{\circ}\text{C}$	$V_{CC33A} = 2.97\text{ V to }3.63\text{ V}$ $I_{LOAD} = 1\text{ mA}$		5.3		mV/V
			$V_{CC33A} = 2.97\text{ V to }3.63\text{ V}$ $I_{LOAD} = 100\text{ mA}$		5.3		mV/V
			$V_{CC33A} = 2.97\text{ V to }3.63\text{ V}$ $I_{LOAD} = 500\text{ mA}$		5.3		mV/V
	Dropout voltage ¹	$T_J = 25^{\circ}\text{C}$	$I_{LOAD} = 1\text{ mA}$		0.63		V
			$I_{LOAD} = 100\text{ mA}$		0.84		V
			$I_{LOAD} = 0.5\text{ A}$		1.35		V
IPTBASE	PTBase current	$T_J = 25^{\circ}\text{C}$	$I_{LOAD} = 1\text{ mA}$		48		μA
			$I_{LOAD} = 100\text{ mA}$		736		μA
			$I_{LOAD} = 0.5\text{ A}$		12		mA
	Startup time ²	$T_J = 25^{\circ}\text{C}$			200		μs

Notes:

1. Dropout voltage is defined as the minimum VCC33A voltage. The parameter is specified with respect to the output voltage. The specification represents the minimum input-to-output differential voltage required to maintain regulation.
2. Assumes 10 μF .

Emcraft Systems provides porting of the open-source U-boot firmware and uClinux™ kernel to the SmartFusion cSoC, a Linux®-based cross-development framework, and other complementary components. Combined with the release of its A2F-Linux Evaluation Kit, this provides a low-cost platform for evaluation and development of Linux (uClinux) on the Cortex-M3 CPU core of the Microsemi SmartFusion cSoC.

- [Emcraft Linux on Microsemi's SmartFusion cSoC](#)

Keil offers the RTX Real-Time Kernel as a royalty-free, deterministic RTOS designed for ARM and Cortex-M devices. It allows you to create programs that simultaneously perform multiple functions and helps to create applications which are better structured and more easily maintained.

- The RTX Real-Time Kernel is included with MDK-ARM. Download the [Evaluation version of Keil MDK-ARM](#).
- RTX source code is available as part of [Keil/ARM Real-Time Library \(RL-ARM\)](#), a group of tightly-coupled libraries designed to solve the real-time and communication challenges of embedded systems based on ARM-powered microcontroller devices. The RL-ARM library now supports SmartFusion cSoCs and designers with additional key features listed in the ["Middleware" section on page 3-5](#).

Micrium supports SmartFusion cSoCs with the company's flagship µC/OS family, recognized for a variety of features and benefits, including unparalleled reliability, performance, dependability, impeccable source code and vast documentation. Micrium supports the following products for SmartFusion cSoCs and continues to work with Microsemi on additional projects.

- [SmartFusion Quickstart Guide for Micrium µC/OS-III Examples](#)
 - [Design Files](#)

µC/OS-III™, Micrium's newest RTOS, is designed to save time on your next embedded project and puts greater control of the software in your hands.

RoweBots provides an ultra tiny Linux-compatible RTOS called Unison for SmartFusion. Unison consists of a set of modular software components, which, like Linux, are either free or commercially licensed. Unison offers POSIX® and Linux compatibility with hard real-time performance, complete I/O modules and an easily understood environment for device driver programming. Seamless integration with FPGA and analog features are fast and easy.

- [Unison V4](#)-based products include a free Unison V4 Linux and POSIX-compatible kernel with serial I/O, file system, six demonstration programs, upgraded documentation and source code for Unison V4, and free (for non-commercial use) Unison V4 TCP/IP server. Commercial license upgrade is available for Unison V4 TCP/IP server with three demonstration programs, DHCP client and source code.
- [Unison V5](#)-based products include commercial Unison V5 Linux- and POSIX-compatible kernel with serial I/O, file system, extensive feature set, full documentation, source code and more than 20 demonstration programs, Unison V5 TCP/IPv4 with extended feature set, sockets interface, multiple network interfaces, PPP support, DHCP client, documentation, source code and six demonstration programs, and multiple other features.

Middleware

Microsemi has ported both uIP and lwIP for Ethernet support as well as including TFTP file service.

- [SmartFusion Webserver Demo Using uIP and FreeRTOS](#)
- [SmartFusion: Running Webserver, TFTP on lwIP TCP/IP Stack Application Note](#)

The [Keil/ARM Real-Time Library \(RL-ARM\)](#)¹, in addition to RTX source, includes the following:

- [RL-TCPnet \(TCP/IP\)](#) – The Keil RL-TCPnet library, supporting full TCP/IP and UDP protocols, is a full networking suite specifically written for small ARM and Cortex-M processor-based microcontrollers. TCPnet is now ported to and supports SmartFusion Cortex-M3. It is highly optimized, has a small code footprint, and gives excellent performance, providing a wide range of application level protocols and examples such as FTP, SNMP, SOAP and AJAX. An [HTTP server example](#) of TCPnet working in a SmartFusion design is available.

1. The CAN and USB functions within RL-ARM are not supported for SmartFusion cSoC.

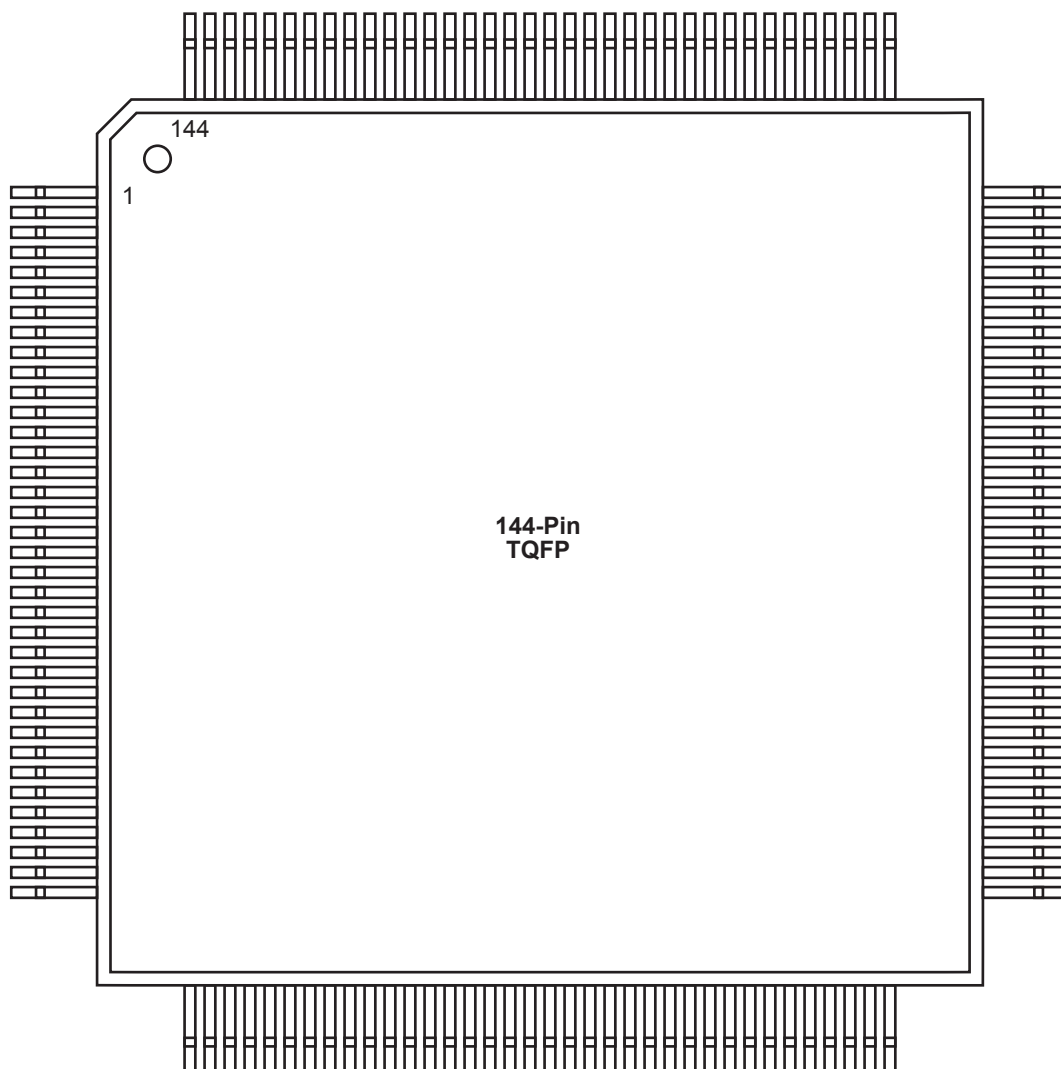
User-Defined Supply Pins

Name	Type	Polarity/ Bus Size	Description
VAREF0	Input	1	<p>Analog reference voltage for first ADC.</p> <p>The SmartFusion cSoC can be configured to generate a 2.56 V internal reference that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREFOUT pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF0 is internally generated, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 μF and 22 μF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF0 signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF0 to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. See the Analog-to-Digital Converter (ADC) section in the SmartFusion Programmable Analog User's Guide for more information. The SoC Products Group recommends customers use 10 μF as the value of the bypass capacitor. Designers choosing to use an external VAREF0 need to ensure that a stable and clean VAREF0 source is supplied to the VAREF0 pin before initiating conversions by the ADC. To use the internal voltage reference, the VAREFOUT pin must be connected to the appropriate ADC VAREF_x input on the PCB. For example, VAREFOUT can be connected to VAREF0 only, if ADC0 alone is used. VAREFOUT can be connected to VAREF1 only, if ADC1 alone is used. VAREFOUT can be connected to VAREF2 only, if ADC2 alone is used. VAREFOUT can be connected to VAREF0, VAREF1 and VAREF2 together, if ADC0, ADC1, and ADC2 all are used.</p>
VAREF1	Input	1	<p>Analog reference voltage for second ADC</p> <p>See "VAREF0" above for more information.</p>
VAREF2	Input	1	<p>Analog reference voltage for third ADC</p> <p>See "VAREF0" above for more.</p>
VAREFOUT	Out	1	<p>Internal 2.56 V voltage reference output. Can be used to provide the two ADCs with a unique voltage reference externally by connecting VAREFOUT to both VAREF0 and VAREF1. To use the internal voltage reference, you must connect the VAREFOUT pin to the appropriate ADC VAREF_x input—either the VAREF0 or VAREF1 pin—on the PCB.</p>

Name	Type	Polarity/Bus Size	Description
NCAP		1	Negative capacitor connection. This is the negative terminal of the charge pump. A capacitor, with a 2.2 μ F recommended value, is required to connect between PCAP and NCAP. Analog charge pump capacitors are not needed if none of the analog SCB features are used and none of the SDDs are used. In that case it should be left unconnected.
PCAP		1	Positive Capacitor connection. This is the positive terminal of the charge pump. A capacitor, with a 2.2 μ F recommended value, is required to connect between PCAP and NCAP. If this pin is not used, it must be left unconnected/floating. In this case, no capacitor is needed. Analog charge pump capacitors are not needed if none of the analog SCB features are used, and none of the SDDs are used.
PTBASE		1	Pass transistor base connection This is the control signal of the voltage regulator. This pin should be connected to the base of an external pass transistor used with the 1.5 V internal voltage regulator and can be floating if not used.
PTEM		1	Pass transistor emitter connection. This is the feedback input of the voltage regulator. This pin should be connected to the emitter of an external pass transistor used with the 1.5 V internal voltage regulator and can be floating if not used.
MSS_RESET_N		Low	Low Reset signal which can be used as an external reset and can also be used as a system level reset under control of the Cortex-M3 processor. MSS_RESET_N is an output asserted low after power-on reset. The direction of MSS_RESET_N changes during the execution of the Microsemi System Boot when chip-level reset is enabled. The Microsemi System Boot reconfigures MSS_RESET_N to become a reset input signal when chip-level reset is enabled. It has an internal pull-up so it can be left floating. In the current software, the MSS_RESET_N is modeled as an external input signal only.
PU_N	In	Low	Push-button is the connection for the external momentary switch used to turn on the 1.5 V voltage regulator and can be floating if not used.

Pin Assignment Tables

TQ144



Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

Pin Number	PQ208	
	A2F200	A2F500
32	VCCRCOSC	VCCRCOSC
33	MSS_RESET_N	MSS_RESET_N
34	VCCESRAM	VCCESRAM
35	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0
36	MAC_MDIO/IO49RSB4V0	MAC_MDIO/IO58RSB4V0
37	MAC_TXEN/IO52RSB4V0	MAC_TXEN/IO61RSB4V0
38	MAC_CRSDV/IO51RSB4V0	MAC_CRSDV/IO60RSB4V0
39	MAC_RXER/IO50RSB4V0	MAC_RXER/IO59RSB4V0
40	GND	GND
41	VCCMSSIOB4	VCCMSSIOB4
42	VCC	VCC
43	MAC_TXD[0]/IO56RSB4V0	MAC_TXD[0]/IO65RSB4V0
44	MAC_TXD[1]/IO55RSB4V0	MAC_TXD[1]/IO64RSB4V0
45	MAC_RXD[0]/IO54RSB4V0	MAC_RXD[0]/IO63RSB4V0
46	MAC_RXD[1]/IO53RSB4V0	MAC_RXD[1]/IO62RSB4V0
47	MAC_CLK	MAC_CLK
48	GNDSDD0	GNDSDD0
49	VCC33SDD0	VCC33SDD0
50	VCC15A	VCC15A
51	PCAP	PCAP
52	NCAP	NCAP
53	VCC33AP	VCC33AP
54	VCC33N	VCC33N
55	SDD0	SDD0
56	GNDA	GNDA
57	GNDAQ	GNDAQ
58	ABPS0	ABPS0
59	ABPS1	ABPS1
60	CM0	CM0
61	TM0	TM0
62	GNDTM0	GNDTM0

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.
2. *: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the [SmartFusion Microcontroller Subsystem User's Guide](#) for more details.